What Is Claimed Is:

1. A semiconductor device comprising:

a semiconductor substrate;

an uppermost metal interconnect formed on the semiconductor substrate;

an oxide layer formed on the substrate and the uppermost metal interconnect;

an aluminum layer formed on the oxide layer; and

a stress-relief layer formed on the aluminum layer.

2. A semiconductor device as defined in claim 1, wherein the stress-relief layer comprises an aluminum oxide layer.

3. A semiconductor device as defined in claim 1, wherein the aluminum layer is formed in a thickness of 100 to 300 Å.

4. A semiconductor device as defined in claim 1, wherein the oxide layer is formed of one of an undoped silica glass and a fluorinated silica glass.

5. A semiconductor device as defined in claim 1, wherein the semiconductor device is at least one of a multi-interconnect adapted device and a power device.

6. A method to fabricate a semiconductor device, the method comprising:

forming an uppermost metal interconnect on a semiconductor substrate;

forming an oxide layer on the substrate and the uppermost metal interconnect;

forming an aluminum layer on the oxide layer; and

forming a stress-relief layer on the aluminum layer to reduce stress on the metal interconnect.

7. A method as defined in claim 6, wherein forming the stress-relief layer comprises:

performing a plasma treatment on a surface of the aluminum layer to form an aluminum oxide layer; and

annealing the aluminum oxide layer.

8. A method as defined in claim 7, wherein the plasma treatment uses at least one of N_2O gas and O_2 gas.

9. A method as defined in claim 7, wherein the annealing is performed at a temperature of 200 to 400℃.

10. A method as defined in claim 7, wherein the aluminum oxide layer is annealed in an atmosphere of inert gas.

11. A method as defined in claim 10, wherein the inert gas is at least one of Ar and He.

12. A method as defined in claim 8, wherein the aluminum oxide layer is annealed in an atmosphere of inert gas.

13. A method as defined in claim 7, wherein the aluminum oxide layer is annealed in an atmosphere of gas including at least one of N_2O, O_2, N_2, and H_2.

14. A method as defined in claim 8, wherein the aluminum oxide layer is annealed in an atmosphere of gas including at least one of N_2O, O_2, N_2, and H_2.

15. A method as defined in claim 6, wherein the semiconductor device is at least one of a multi-interconnect adapted device and a power device.